

AMENDMENT(S) TO THE SPECIFICATION

Please replace paragraph number [0006] at page 2 with the following rewritten paragraph:

CU [0006] A process and structure which prevents punch-through without increasing channel dose or channel depth would be very desirable before avalanche voltage is reached.

Please replace paragraph number [0015] at page 3 with the following rewritten paragraph:

CR [0015] The implant dose and diffusion drive time will determine the conductivity and depth of the channel regions ~~25~~ 24. At the same time that windows are opened in layer 16, a conductive polysilicon field plate 26 (an extension of layer 16) is also defined in the termination region.